



# PHPT60606PY

60 V, 6 A PNP high power bipolar transistor

9 December 2014

Product data sheet

## 1. General description

PNP high power bipolar transistor in a SOT669 (LFPK56) Surface-Mounted Device (SMD) power plastic package.

NPN complement: PHPT60606NY.

## 2. Features and benefits

- High thermal power dissipation capability
- Suitable for high temperature applications up to 175 °C
- Reduced Printed-Circuit Board (PCB) requirements comparing to transistors in DPAK
- High energy efficiency due to less heat generation
- AEC-Q101 qualified

## 3. Applications

- Power management
- Load switch
- Linear mode voltage regulator
- Backlighting applications
- Motor drive
- Relay replacement

## 4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$V_{CEO}$	collector-emitter voltage	open base	-	-	-60	V
$I_C$	collector current		-	-	-6	A
$I_{CM}$	peak collector current	$t_p \leq 1$ ms; pulsed	-	-	-12	A
$R_{CEsat}$	collector-emitter saturation resistance	$I_C = -6$ A; $I_B = -600$ mA; pulsed; $t_p \leq 300$ $\mu$ s; $\delta \leq 0.02$ ; $T_{amb} = 25$ °C	-	66	88	m $\Omega$

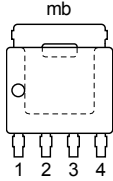
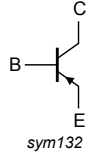


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## 5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	E	emitter	 <p><b>LFPAK56; Power-SO8 (SOT669)</b></p>	
2	E	emitter		
3	E	emitter		
4	B	base		
mb	C	collector		

## 6. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
PHPT60606PY	LFPAK56; Power-SO8	Plastic single-ended surface-mounted package (LFPAK56; Power-SO8); 4 leads	SOT669

## 7. Marking

Table 4. Marking codes

Type number	Marking code
PHPT60606PY	0606PAB

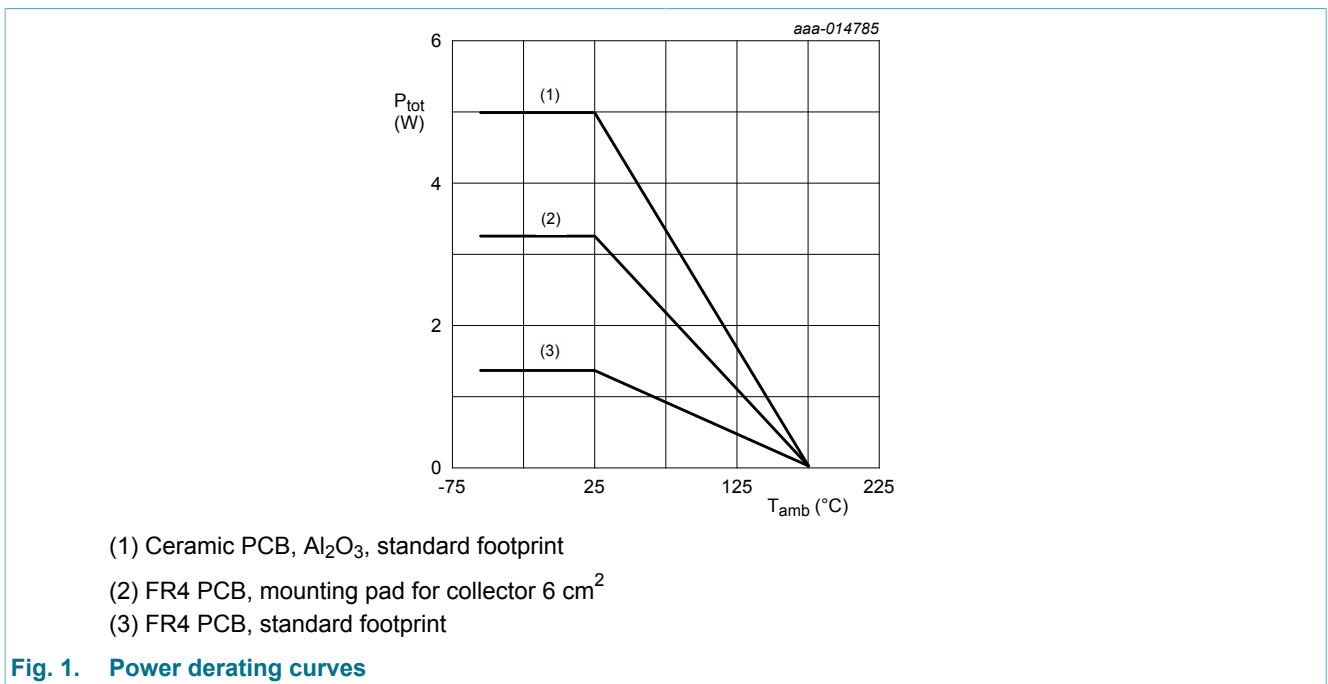
## 8. Limiting values

**Table 5. Limiting values**

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
$V_{CBO}$	collector-base voltage	open emitter		-	-60	V
$V_{CEO}$	collector-emitter voltage	open base		-	-60	V
$V_{EBO}$	emitter-base voltage	open collector		-	-8	V
$I_C$	collector current			-	-6	A
$I_{CM}$	peak collector current	$t_p \leq 1$ ms; pulsed		-	-12	A
$I_B$	base current			-	-800	mA
$I_{BM}$	peak base current	$t_p \leq 1$ ms; pulsed		-	-1.2	A
$P_{tot}$	total power dissipation	$T_{amb} \leq 25$ °C	[1]	-	1.35	W
			[2]	-	3.25	W
			[3]	-	5	W
			[4]	-	25	W
$T_j$	junction temperature			-	175	°C
$T_{amb}$	ambient temperature			-55	175	°C
$T_{stg}$	storage temperature			-65	175	°C

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated mounting pad for collector 6 cm<sup>2</sup>.
- [3] Device mounted on a ceramic PCB, Al<sub>2</sub>O<sub>3</sub>, standard footprint.
- [4] Power dissipation from junction to mounting base.



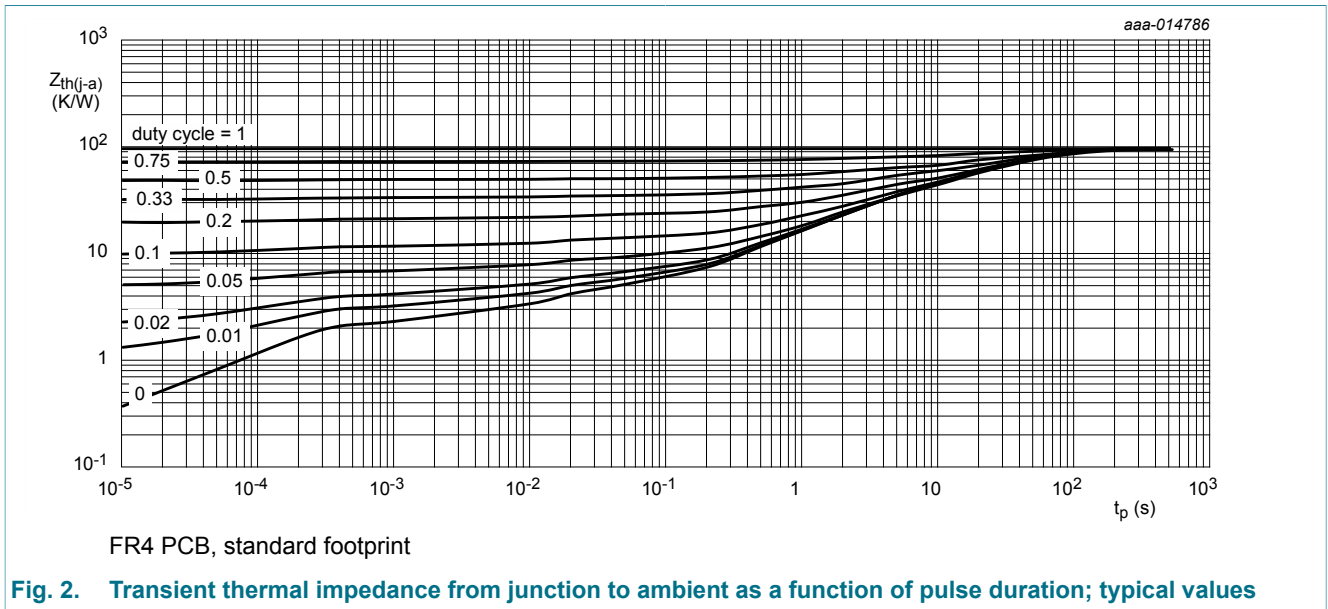
**Fig. 1. Power derating curves**

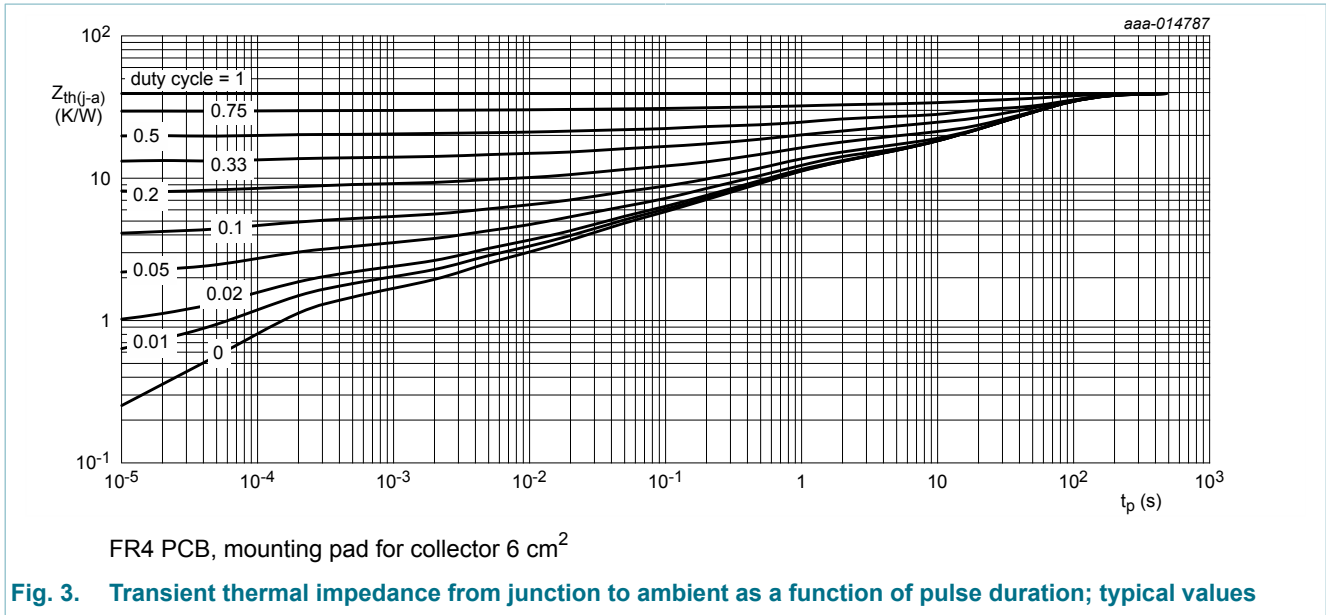
## 9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	[1]	-	-	111	K/W
			[2]	-	-	46	K/W
			[3]	-	-	30	K/W
$R_{th(j-mb)}$	thermal resistance from junction to mounting base			-	-	6	K/W

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated mounting pad for collector 6 cm<sup>2</sup>.
- [3] Device mounted on a ceramic PCB, Al<sub>2</sub>O<sub>3</sub>, standard footprint.



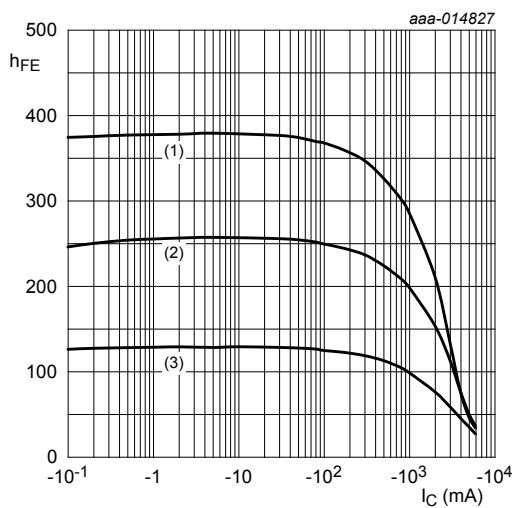


## 10. Characteristics

Table 7. Characteristics

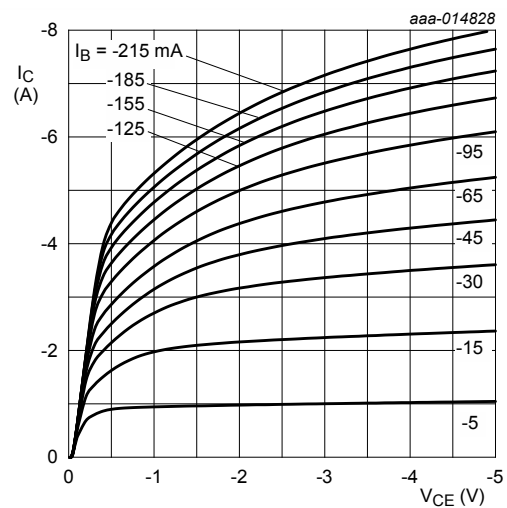
Symbol	Parameter	Conditions	Min	Typ	Max	Unit
I <sub>CBO</sub>	collector-base cut-off current	V <sub>CB</sub> = -48 V; I <sub>E</sub> = 0 A; T <sub>amb</sub> = 25 °C	-	-	-100	nA
		V <sub>CB</sub> = -48 V; I <sub>E</sub> = 0 A; T <sub>j</sub> = 150 °C	-	-	-50	μA
I <sub>CES</sub>	collector-emitter cut-off current	V <sub>CE</sub> = -48 V; V <sub>BE</sub> = 0 V; T <sub>amb</sub> = 25 °C	-	-	-100	nA
I <sub>EBO</sub>	emitter-base cut-off current	V <sub>EB</sub> = -8 V; I <sub>C</sub> = 0 A; T <sub>amb</sub> = 25 °C	-	-	-100	nA
h <sub>FE</sub>	DC current gain	V <sub>CE</sub> = -2 V; I <sub>C</sub> = -500 mA; T <sub>amb</sub> = 25 °C	120	200	-	
		V <sub>CE</sub> = -2 V; I <sub>C</sub> = -1 A; t <sub>p</sub> ≤ 300 μs; δ ≤ 0.02; T <sub>amb</sub> = 25 °C; pulsed	110	180	-	
		V <sub>CE</sub> = -2 V; I <sub>C</sub> = -3 A; t <sub>p</sub> ≤ 300 μs; δ ≤ 0.02; T <sub>amb</sub> = 25 °C; pulsed	60	100	-	
		V <sub>CE</sub> = -2 V; I <sub>C</sub> = -6 A; pulsed; t <sub>p</sub> ≤ 300 μs; δ ≤ 0.02; T <sub>amb</sub> = 25 °C	20	30	-	
V <sub>CEsat</sub>	collector-emitter saturation voltage	I <sub>C</sub> = -1 A; I <sub>B</sub> = -50 mA; t <sub>p</sub> ≤ 300 μs; δ ≤ 0.02; T <sub>amb</sub> = 25 °C	-	-75	-110	mV
		I <sub>C</sub> = -3 A; I <sub>B</sub> = -300 mA; t <sub>p</sub> ≤ 300 μs; δ ≤ 0.02; T <sub>amb</sub> = 25 °C; pulsed	-	-155	-230	mV
		I <sub>C</sub> = -6 A; I <sub>B</sub> = -600 mA; pulsed; t <sub>p</sub> ≤ 300 μs; δ ≤ 0.02; T <sub>amb</sub> = 25 °C	-	-395	-525	mV
R <sub>CEsat</sub>	collector-emitter saturation resistance	I <sub>C</sub> = -6 A; I <sub>B</sub> = -600 mA; pulsed; t <sub>p</sub> ≤ 300 μs; δ ≤ 0.02; T <sub>amb</sub> = 25 °C	-	66	88	mΩ

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$V_{BEsat}$	base-emitter saturation voltage	$I_C = -1\text{ A}; I_B = -50\text{ mA};$ pulsed; $t_p \leq 300\ \mu\text{s}; \delta \leq 0.02; T_{amb} = 25\text{ }^\circ\text{C}$	-	-0.85	-0.95	V
		$I_C = -3\text{ A}; I_B = -300\text{ mA};$ pulsed; $t_p \leq 300\ \mu\text{s}; \delta \leq 0.02; T_{amb} = 25\text{ }^\circ\text{C}$	-	-1	-1.1	V
		$I_C = -6\text{ A}; I_B = -600\text{ mA};$ pulsed; $t_p \leq 300\ \mu\text{s}; \delta \leq 0.02; T_{amb} = 25\text{ }^\circ\text{C}$	-	-1.1	-1.3	V
$V_{BEon}$	base-emitter turn-on voltage	$V_{CE} = -2\text{ V}; I_C = -0.5\text{ A}; T_{amb} = 25\text{ }^\circ\text{C}$	-	-0.75	-0.85	V
$t_d$	delay time	$V_{CC} = -12.5\text{ V}; I_C = -3\text{ A};$ $I_{Bon} = -150\text{ mA}; I_{Boff} = 150\text{ mA};$ $T_{amb} = 25\text{ }^\circ\text{C}$	-	15	-	ns
$t_r$	rise time		-	110	-	ns
$t_{on}$	turn-on time		-	125	-	ns
$t_s$	storage time		-	185	-	ns
$t_f$	fall time		-	70	-	ns
$t_{off}$	turn-off time		-	255	-	ns
$f_T$	transition frequency		$V_{CE} = -10\text{ V}; I_C = -500\text{ mA};$ $f = 100\text{ MHz}; T_{amb} = 25\text{ }^\circ\text{C}$	-	110	-
$C_c$	collector capacitance	$V_{CB} = -10\text{ V}; I_E = 0\text{ A}; i_e = 0\text{ A};$ $f = 1\text{ MHz}; T_{amb} = 25\text{ }^\circ\text{C}$	-	57	-	pF



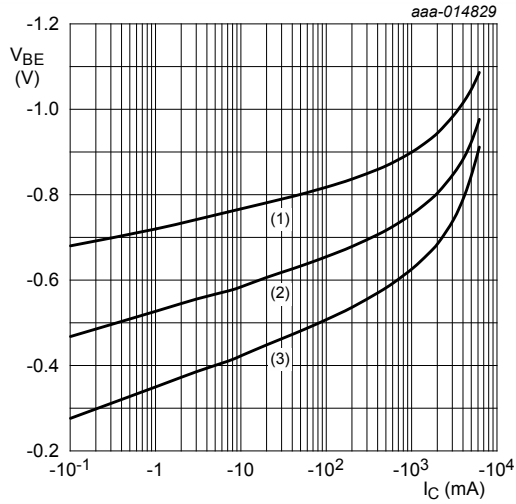
$V_{CE} = -2\text{ V}$   
 (1)  $T_{amb} = 100\text{ }^\circ\text{C}$   
 (2)  $T_{amb} = 25\text{ }^\circ\text{C}$   
 (3)  $T_{amb} = -55\text{ }^\circ\text{C}$

**Fig. 4. DC current gain as a function of collector current; typical values**



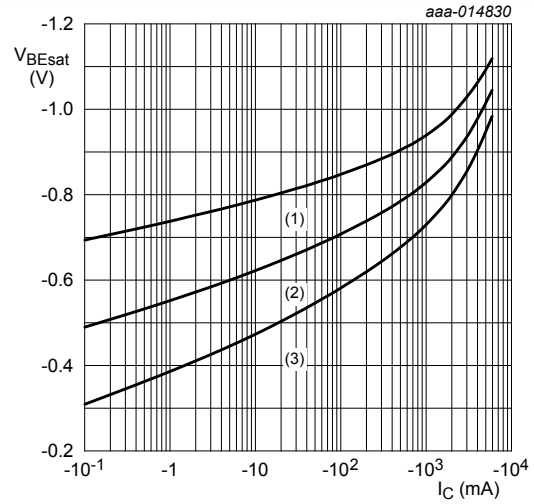
$T_{amb} = 25\text{ }^\circ\text{C}$

**Fig. 5. Collector current as a function of collector-emitter voltage; typical values**



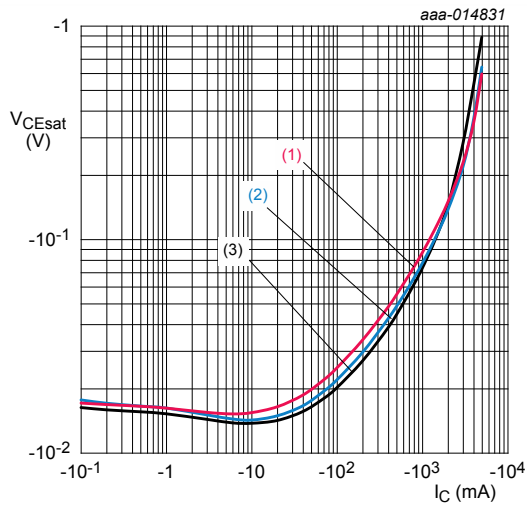
$V_{CE} = -2 \text{ V}$   
 (1)  $T_{amb} = -55 \text{ }^\circ\text{C}$   
 (2)  $T_{amb} = 25 \text{ }^\circ\text{C}$   
 (3)  $T_{amb} = 100 \text{ }^\circ\text{C}$

**Fig. 6. Base-emitter voltage as a function of collector current; typical values**



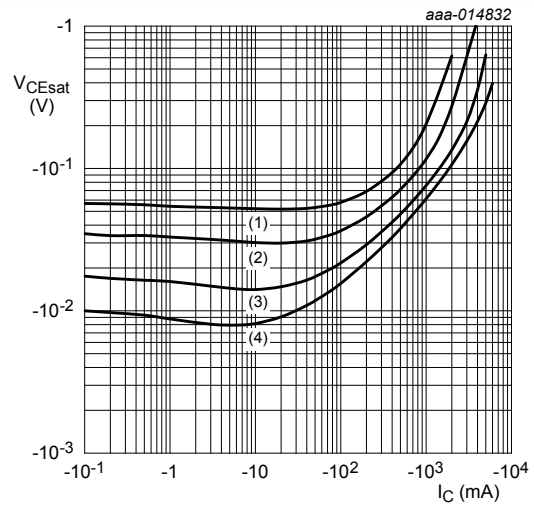
$I_C/I_B = 20$   
 (1)  $T_{amb} = -55 \text{ }^\circ\text{C}$   
 (2)  $T_{amb} = 25 \text{ }^\circ\text{C}$   
 (3)  $T_{amb} = 100 \text{ }^\circ\text{C}$

**Fig. 7. Base-emitter saturation voltage as a function of collector current; typical values**



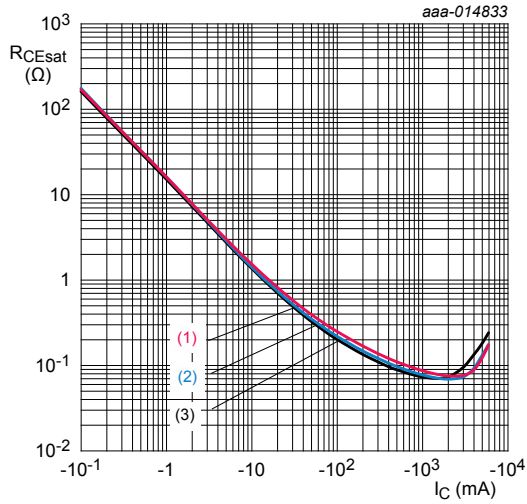
$I_C/I_B = 20$   
 (1)  $T_{amb} = 100 \text{ }^\circ\text{C}$   
 (2)  $T_{amb} = 25 \text{ }^\circ\text{C}$   
 (3)  $T_{amb} = -55 \text{ }^\circ\text{C}$

**Fig. 8. Collector-emitter saturation voltage as a function of collector current; typical values**



$T_{amb} = 25 \text{ }^\circ\text{C}$   
 (1)  $I_C/I_B = 100$   
 (2)  $I_C/I_B = 50$   
 (3)  $I_C/I_B = 20$   
 (4)  $I_C/I_B = 10$

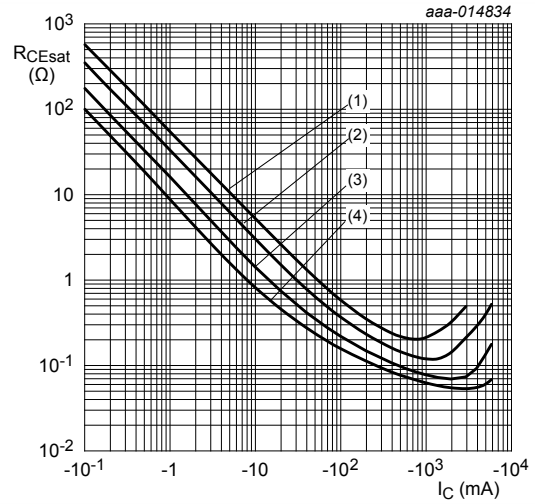
**Fig. 9. Collector-emitter saturation voltage as a function of collector current; typical values**



$I_C/I_B = 20$

- (1)  $T_{amb} = 100\text{ °C}$
- (2)  $T_{amb} = 25\text{ °C}$
- (3)  $T_{amb} = -55\text{ °C}$

**Fig. 10. Collector-emitter saturation resistance as a function of collector current; typical values**



$T_{amb} = 25\text{ °C}$

- (1)  $I_C/I_B = 100$
- (2)  $I_C/I_B = 50$
- (3)  $I_C/I_B = 20$
- (4)  $I_C/I_B = 10$

**Fig. 11. Collector-emitter saturation resistance as a function of collector current; typical values**



### 11. Test information

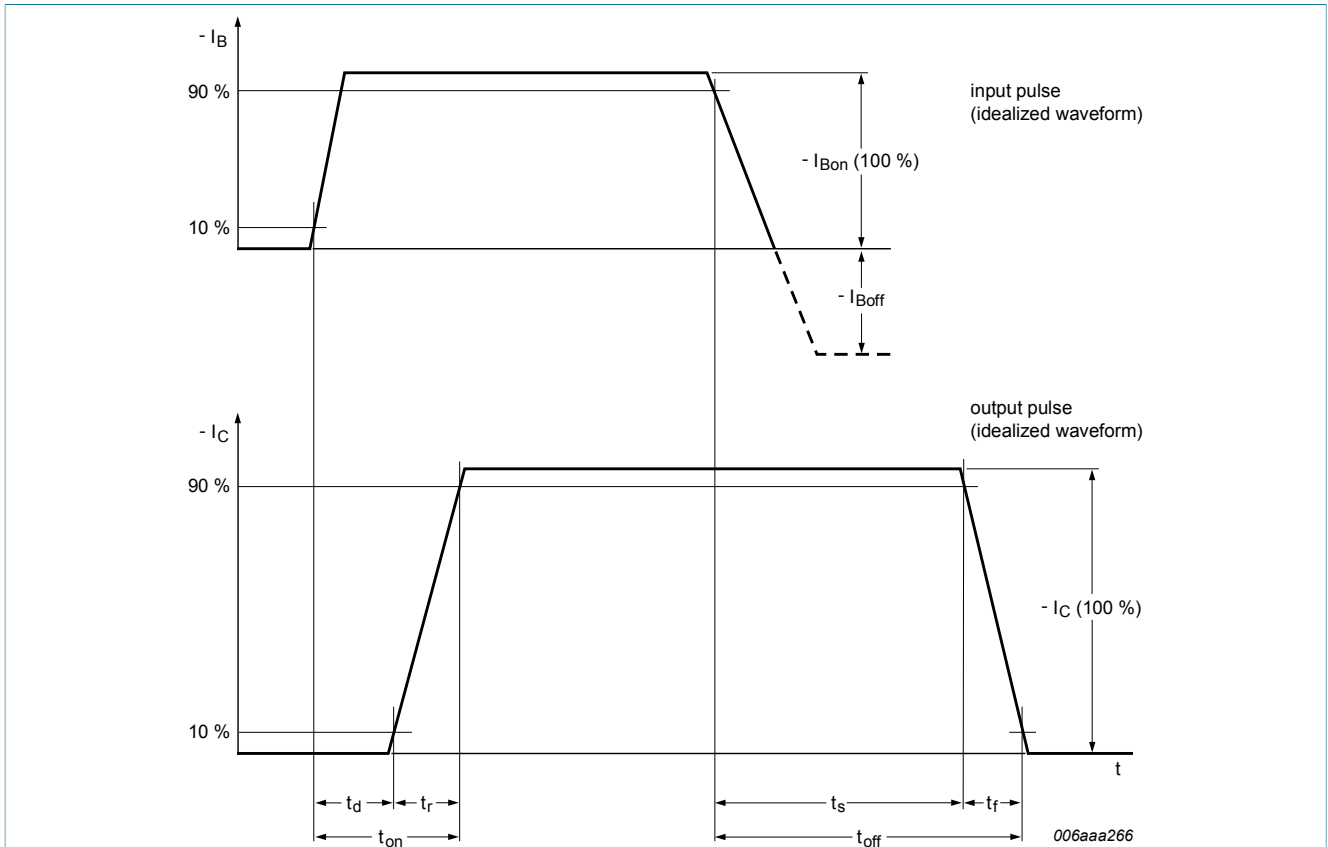


Fig. 12. BISS transistor switching time definition

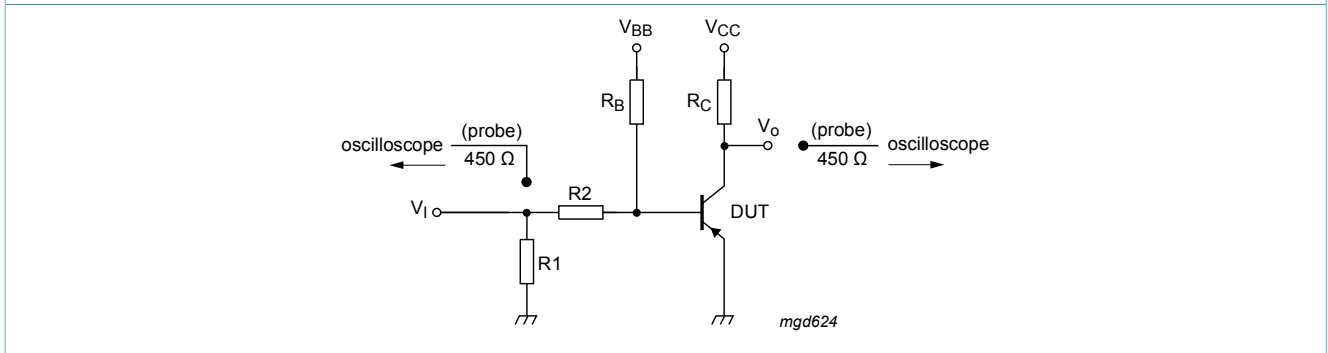


Fig. 13. Test circuit for switching times

#### 11.1 Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard Q101 - *Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

12. Package outline



Fig. 14. Package outline LFAK56; Power-SO8 (SOT669)

### 13. Soldering

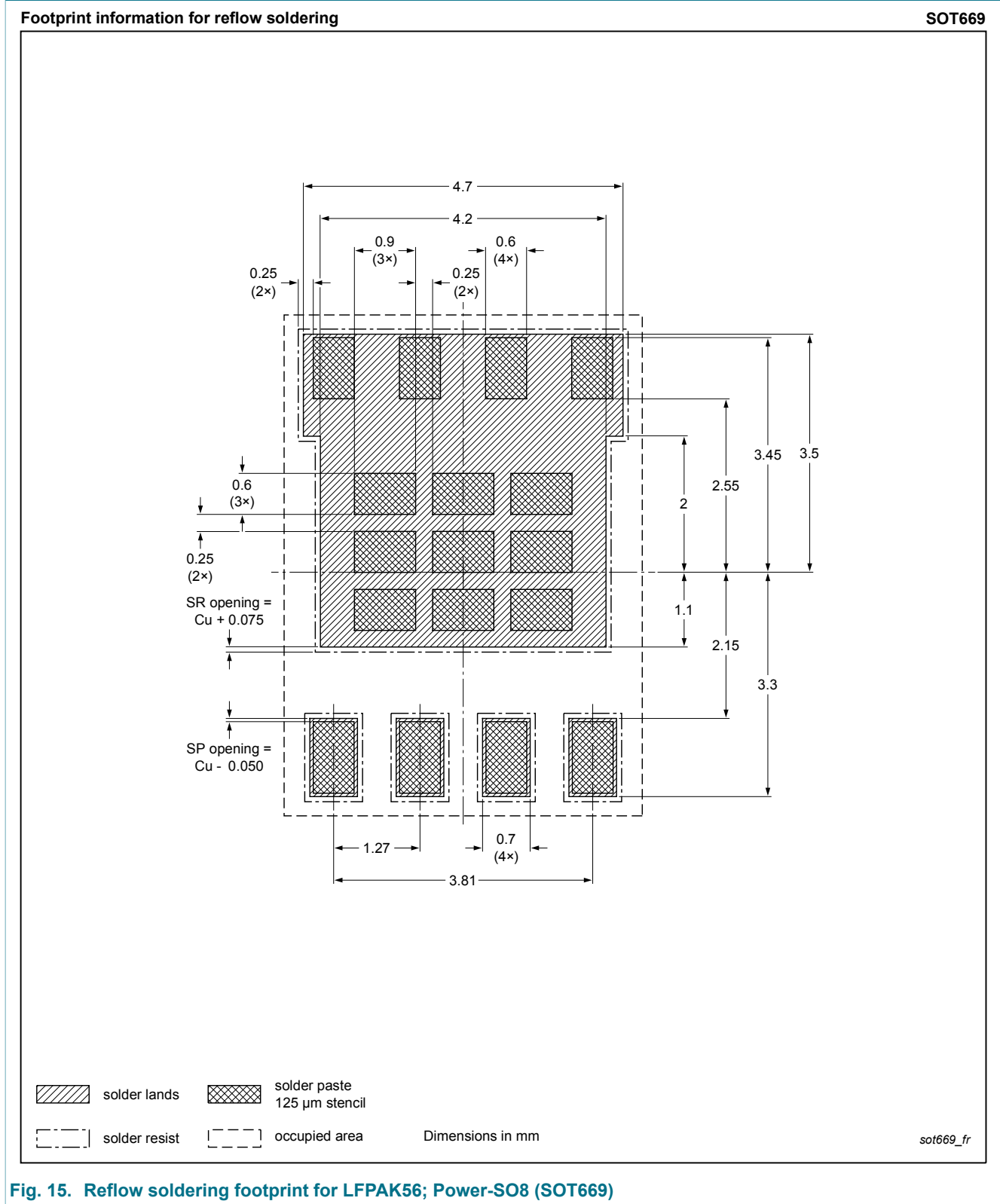


Fig. 15. Reflow soldering footprint for LFPAK56; Power-SO8 (SOT669)

## 14. Revision history

Table 8. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
PHPT60606PY v.1	20141209	Product data sheet	-	-

## 15. Legal information

### 15.1 Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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- [2] The term 'short data sheet' is explained in section "Definitions".
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